Sure, here are six research papers on the topic of “Tunneling Phenomena in Ultra-Thin Oxide MOS Structures” that you might find helpful for your review paper and presentation:

1. [“A review of gate tunneling current in MOS devices” - This paper studies the physical mechanisms of tunneling in an MOS structure, along with the particularities of tunneling in modern MOS transistors1](https://www.ece.mcmaster.ca/~chihhung/Publication/MR_46_Gate_Tunneling.pdf).
2. [“Tunneling in thin MOS structures” - This research article provides recent results on tunneling in thin MOS structures2](https://pubs.aip.org/avs/jvst/article/11/6/996/249130/Tunneling-in-thin-MOS-structures).
3. [“Electrical Characterization of Metal-Oxide-Silicon Structures with Very Thin Oxide Layers” - This paper discusses the electrical characterization of MOS structures with very thin (2 - 4 nm) oxide layers3](https://research.chalmers.se/en/publication/1060).
4. [“Full-band approaches to the electronic properties of nanometer-scale MOS structures” - This paper uses quantum mechanical methods that include the full-band structure of Si and SiO2 to study two non-classical phenomena that occur in MOS transistors at the nanometer-scale: tunneling through ultrathin oxides and quantum confinement in Si layers4](https://www.academia.edu/3696383/Full_band_approaches_to_the_electronic_properties_of_nanometer_scale_MOS_structures).
5. [“Study of tunneling current through ultra-thin gate oxide MOSFET and its effect on CMOS circuits” - In this paper, a numerical model has been constructed to study the tunneling current through ultra-thin gate oxide MOSFET and the effect of this tunneling current on the MOSFET and on the performance of CMOS circuits5](https://www.academia.edu/56518745/Study_of_tunneling_current_through_ultra_thin_gate_oxide_MOSFET_and_its_effect_on_CMOS_circuits).
6. [“Modeling and simulation of tunneling through ultra-thin gate dielectrics” - This paper models Direct and Fowler-Nordheim tunneling through ultra-thin gate dielectrics based on an approach for the transmission coefficient (TC) of a potential barrier that is modified by the image force1](https://www.ece.mcmaster.ca/~chihhung/Publication/MR_46_Gate_Tunneling.pdf).

I hope these papers will be useful for your review paper and presentation! Let me know if you need help with anything else.